

Drift Mobility and Electric Field in Silicon Detectors Irradiated with Neutrons and Protons up to $1E17$ n_{eq}/cm^2 [Thu/Friday]

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Electric field in silicon irradiated with neutrons up to $1e17$ n_{eq}/cm^2 and PS protons up to $3e16$ p/cm^2 was investigated by edge-TCT. Methods for absolute determination of electric field were developed and electric field profiles in the silicon bulk obtained. From the $v(E)$ dependence mobility degradation with fluence was extracted. A $1/\sqrt{\Phi}$ dependence of mobility on fluence was observed for both irradiations with protons provoking ~ 20 % more degradation at equal NIEL. The observed mobility degradation and the values of electric field indicate substantial reduction of trapping from linear extrapolation of low fluence values.

Primary author: MIKUZ, Marko (Jozef Stefan Institute (SI))

Co-authors: KRAMBERGER, Gregor (Jozef Stefan Institute (SI)); MANDIC, Igor (Jozef Stefan Institute (SI)); ZAVRTANIK, Marko (Jozef Stefan Institute (SI)); CINDRO, Vladimir (Jozef Stefan Institute (SI))

Presenter: MIKUZ, Marko (Jozef Stefan Institute (SI))

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